

Appl. No. 10/684,108
Examiner: Asok K. Sarkar, Art Unit 2891
In response to the Office Action dated April 7, 2005

Date: July 7, 2005
Attorney Docket No. 10113041

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph at page 2, line 13 with the following amended paragraph:

– FIG. 1b is a top view of multiple layers formed by the first mask, wherein the layers are the metal wire layers 11a. ~~FIG. 1c is a C-C cross section of FIG. 1b.~~ In FIG. 1b, first marks 101 and 102 are formed on the X and Y axes of the first mask layer 11 respectively. The first marks 101 and 102 align exactly with the alignment mark of the wafer to form the corresponding first marks 111 and 112 of the metal wire layer 11a.

Please insert the following new paragraph at page 2, line 21, after the paragraph ending with "the metal wire layer 11a":

–FIG. 1c is a cross section of the wafer with multiple layers formed by the first mask 11 where photolithography is performed.

Please replace the paragraph at page 2, line 21 with the following amended paragraph:

– FIG. 1d is a top view of the multiple layers formed by the second mask, comprising metal wire layers 11a. FIG. 1e is a top view of the pattern formed by the second mask on the pattern formed by the first mask. ~~FIG. 1f is a C-C cross section of FIG. 1d.~~ FIG. 1f is a cross section of the wafer with multiple layers formed by the second mask where photolithography is performed.

Please replace the paragraph at page 7, line 8 with the following amended paragraph:

– FIG. 2g is a cross-section of ~~FIG. 2f.~~ the wafer which is deformed.